

EAST - [10694889.wsp:1]

File View Edit Tools Window Help

Drafts  
BRS  
Pending  
Active

- L1: (2387) heterojunction and (emitter and base and collector)
- L2: (3) (heterojunction and (emitter and base and collector)) with lattice near constant\$1
- L3: (3) (heterojunction and (emitter and base and collector)) with (lattice near constant\$1)
- L4: (29) (emitter and base and collector) with (lattice near constant\$1)
- L5: (204871) collector
- L6: (91346) lattice
- L7: (435) 5 with 6
- L8: (1304226) constant\$1
- L9: (10411) 6 near4 8
- L10: (2375288) value or values
- L11: (6) 9 with 5 with 10
- L12: (57) 9 with 5
- L13: (18) (heterojunction near bipolar near transistor or 'HBT') and ((collector and base and em
- L14: (231) heterojunction and (InGaP/GaAs or InP/InGaAs)
- L15: (172) heterojunction near bipolar and (InGaP/GaAs or InP/InGaAs)
- L16: (24) (heterojunction near bipolar near transistor or 'HBT') and (InGaP/GaAs and InP/InGaA

Failed

- (0) 10 with (different near lattice near constant\$1)
- (0) 2 with (lattice near constant\$1)
- (0) 2 with (lattice near constant\$1)
- (0) 2 near (lattice near constant\$1)
- (0) 2 near (lattice near constant\$1)
- (0) 1 with 2
- (0) 1 with 2

Saved

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DBs Plurals

Default op Highlight all hit terms initially

(heterojunction near bipolar near transistor or 'HBT') and ((collector and base and emitter) with (lattice near constant\$1))

ABR AS Im Text HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20040113143 A1	20040617	15	Semiconductor device having a lattice-mismatched semiconductor layer on	257/22	257/197; 257/201
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20040104403 A1	20040603	13	Thin gallium-arsenide-antimonide base heterojunction bipolar transistor (HBT)	257/183	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20040089875 A1	20040513	21	Heterojunction bipolar transistor	257/183	
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20020145137 A1	20021010	14	Thin gallium-arsenide-antimonide base heterojunction bipolar transistor (HBT)	257/19	257/E29.033; 257/E29.044;
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20020093031 A1	20020718	18	Heterojunction bipolar transistor	257/200	257/201; 257/586;
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20020038898 A1	20020404	25	Semiconductor device and method of producing the same	257/378	257/E21.703; 257/E27.112
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6762480 B2	20040713	15	Thin gallium-arsenide-antimonide base heterojunction bipolar transistor (HBT)	257/592	
8	<input type="checkbox"/>	<input type="checkbox"/>	US 6509587 B2	20030121	23	Semiconductor device	257/192	257/190; 257/194;
9	<input type="checkbox"/>	<input type="checkbox"/>	US 6509242 B2	20030121	17	Heterojunction bipolar transistor	438/312	257/200; 257/565;
10	<input type="checkbox"/>	<input type="checkbox"/>	US 5841156 A	19981124	17	Semiconductor device including T1 GaAs layer	257/183	257/184; 257/194;
11	<input type="checkbox"/>	<input type="checkbox"/>	US 5679964 A	19971021	19	Optoelectronic integrated device	257/83	257/13; 257/190;